

GaAlAs-IR-Lumineszenzdiode (880 nm) und grüne GaP-LED (565 nm) GaAlAs-Infrared-Emitter (880 nm) and green GaP-LED (565 nm)

SFH 7222



Wesentliche Merkmale

- SMT-Gehäuse mit IR-Sender (880 nm) und grünem Sender (565 nm)
- Geeignet für SMT-Bestückung
- Gegurtet lieferbar
- Sender und Empfänger getrennt ansteuerbar
- Geeignet für IR-Reflow Löten

Features

- SMT package with IR emitter (880 nm) and green emitter (565 nm)
- Suitable for SMT assembly
- Available on tape and reel
- Emitter und detector can be controlled separately
- Suitable for IR reflow soldering

Anwendungen

- Kombination von Anzeigeelement mit:
 - Datenübertragung
 - Fernsteuerung
 - Infrarotschnittstelle

Applications

- Combination of display with:
 - data transmission
 - remote control
 - infrared interface

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
SFH 7222	Q62702-P5095	SMT Multi TOPLED®

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		IRE D	LED	
Betriebstemperatur Operating temperature range	T_{op}	– 40 ... + 100	– 40 ... + 100	°C
Lagertemperatur Storage temperature range	T_{stg}	– 40 ... + 100	– 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	5	5	V
Durchlaßstrom Forward current	I_F (DC)	100	30	mA
Stoßstrom Surge current $t_p \leq 10 \mu s, D = 0$	I_{FSM}	2.5	0.5	A
Verlustleistung Total power dissipation	P_{tot}	180	100	mW
Wärmewiderstand Thermal resistance junction/ambient ¹⁾	$R_{th JA}$	450	500	K/W
Wärmewiderstand Thermal resistance junction/ambient ²⁾	$R_{th JA}$	650		K/W

¹⁾ nur ein Chip betrieben / only one chip on

²⁾ beide Chips betrieben / both chips on

Hinweis/Notes

Die angegebenen Grenzdaten gelten für einen Chip, wenn nicht anders angegeben.
 The stated maximum ratings refer to one chip, unless otherwise specified.

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		IRED	LED	
Wellenlänge der Strahlung Wavelength of peak emission $I_F = 100\text{ mA}$	λ_{peak}	880	565 ($I_F = 10\text{ mA}$)	nm
Dominantwellenlänge Dominant wavelength $I_F = 10\text{ mA}$	λ_{dom}	–	570	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100\text{ mA}$	$\Delta\lambda$	80	25 ($I_F = 10\text{ mA}$)	nm
Abstrahlwinkel Half angle	φ	± 60	± 60	Grad deg.
Abmessungen der aktiven Chipfläche Dimensions of the active chip area	$L \times B$ $L \times W$	0.4×0.4	0.25×0.25	mm ²
Schaltzeiten Switching times 10%/90%, $I_F = 100\text{ mA}$, $R_L = 50\ \Omega$	t_r, t_f	500	450, 200	ns
Kapazität Capacitance $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_o	25	15	pF
Durchlaßspannung Forward voltage $I_F = 10\text{ mA}$ $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$, $t_p = 100\ \mu\text{s}$	V_F	– 1.5 (≤ 1.8) 3.0 (≤ 3.8)	2.0 (≤ 2.6) – –	V
Sperrstrom, $V_R = 5\text{ V}$ Reverse current	I_R	0.01 (≤ 1)	0.01 (≤ 10)	μA
Gesamtstrahlungsfluß Total radiant flux $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	Φ_e	23	–	mW
Lichtstärke Luminous intensity $I_F = 2\text{ mA}$	I_v	–	8 (> 4)	mcd
Temperaturkoeffizient von I_e bzw. Φ_e Temperature coefficient of I_e or Φ_e $I_F = 100\text{ mA}$	TC_I	– 0.5	– 0.3	%/K

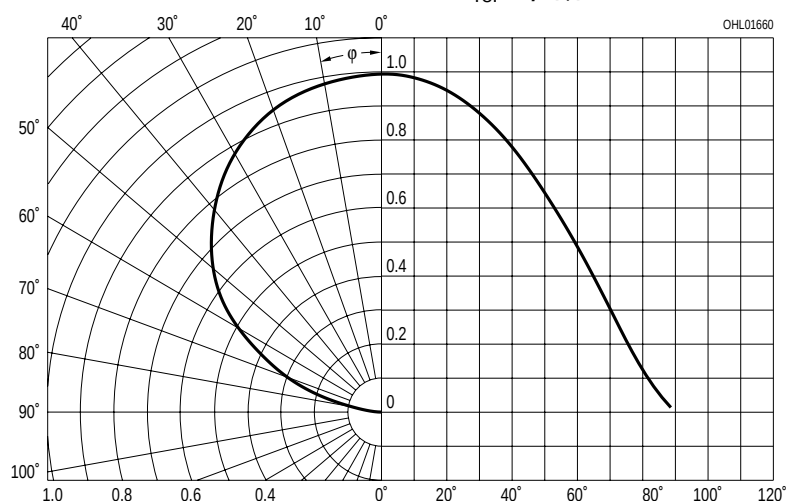
Kennwerte ($T_A = 25\text{ °C}$)

Characteristics (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		IRED	LED	
Temperaturkoeffizient von V_F Temperature coefficient of V_F $I_F = 100\text{ mA}$	TC_V	- 2	- 1.4	mV/K
Temperaturkoeffizient von λ Temperature coefficient of λ $I_F = 100\text{ mA}$	TC_λ	+ 0.25	$0.3 \times \lambda_{\text{peak}}$ $0.07 \times \lambda_{\text{dom}}$	nm/K

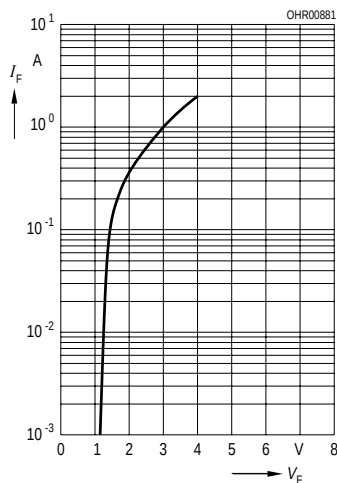
Strahlstärke I_e der IRED in Achsrichtunggemessen bei einem Raumwinkel $\Omega = 0.01\text{ sr}$ Radiant Intensity I_e of the IRED in Axial Directionat a solid angle of $\Omega = 0.01\text{ sr}$

Bezeichnung Description	Symbol Symbol	Werte Values	Einheit Unit
Strahlstärke Radiant intensity $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	$I_{e\text{ min.}}$	≥ 4	mW/sr
Strahlstärke Radiant intensity $I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	$I_{e\text{ typ.}}$	48	mW/sr

IRED Radiation Characteristics $I_{\text{rel}} = f(\varphi)$ LED Directional Characteristics $S_{\text{rel}} = f(\varphi)$ 

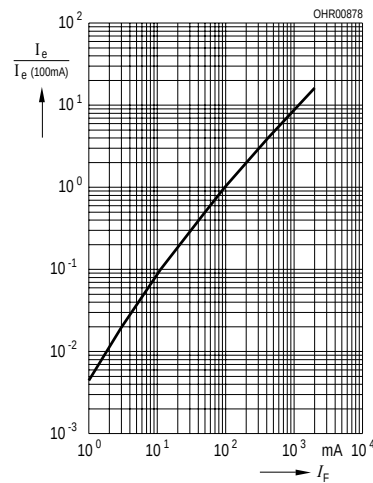
URED

Forward Current $I_F = f(V_F)$
 $T_A = 25\text{ °C}$

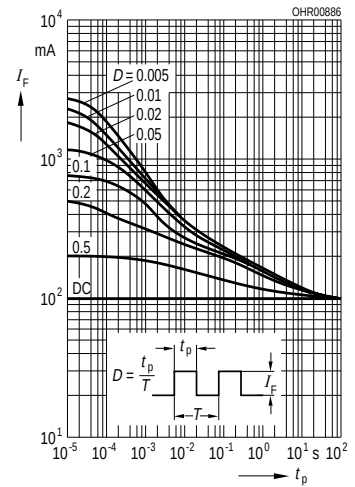


Rel Luminous Intensity

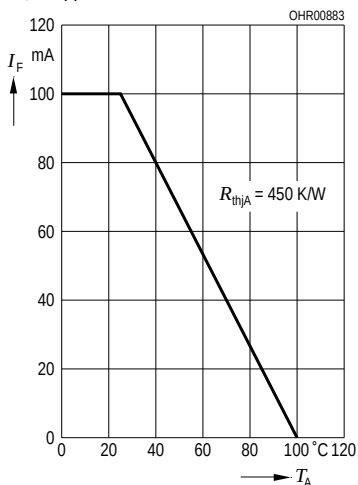
$I_V / I_{V(10\text{ mA})} = f(I_F)$
 $T_A = 25\text{ °C}$



Perm. Pulse Handling Capability
 $I_F = f(t_p)$, Duty cycle $D = \text{parameter}$,
 $T_A = 25\text{ °C}$

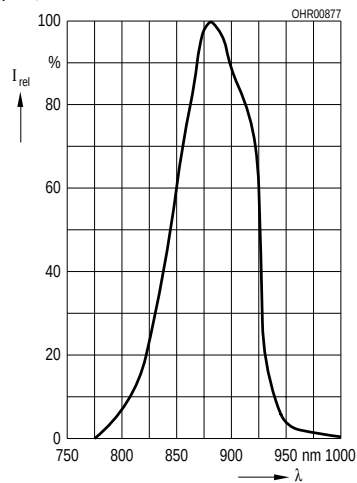


Max. Permissible Forward Current
 $I_F = f(T_A)$



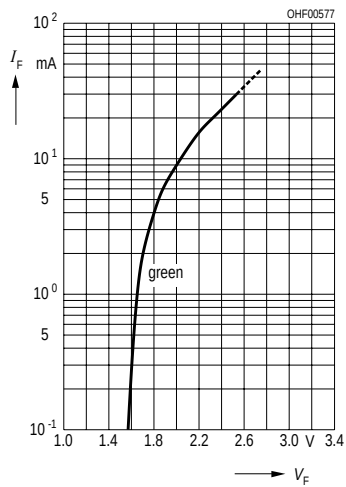
Relative Spectral Emission

$I_{\text{rel}} = f(\lambda)$

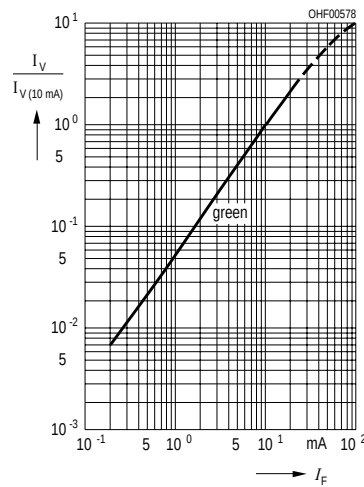


LED

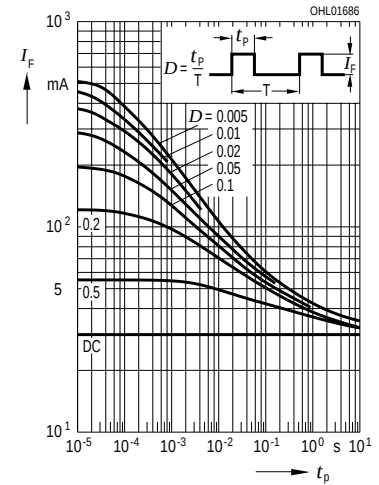
Forward Current $I_F = f(V_F)$
 $T_A = 25\text{ °C}$



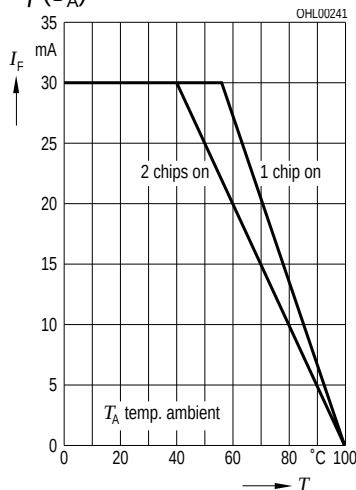
Relative Luminous Intensity
 $I_V / I_{V(10\text{ mA})} = f(I_F, T_A = 25\text{ °C})$



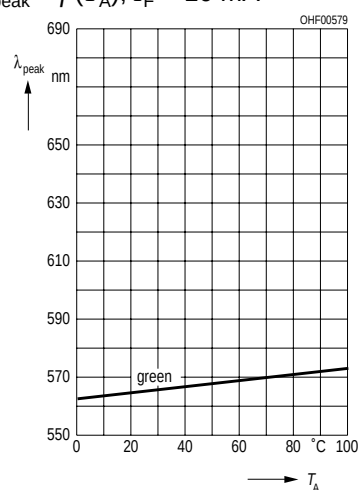
Perm. Pulse Handling Capability
 $I_F = f(t_p)$
 Duty cycle $D = \text{parameter}$, $T_A = 25\text{ °C}$



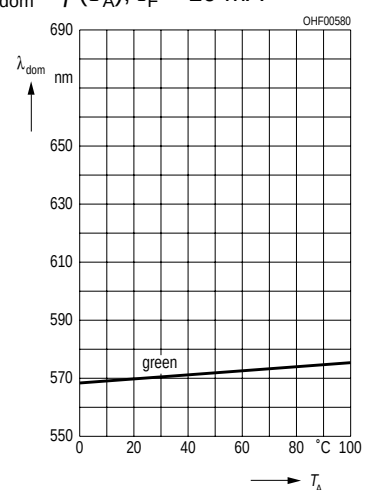
Max. Permissible Forward Current
 $I_F = f(T_A)$



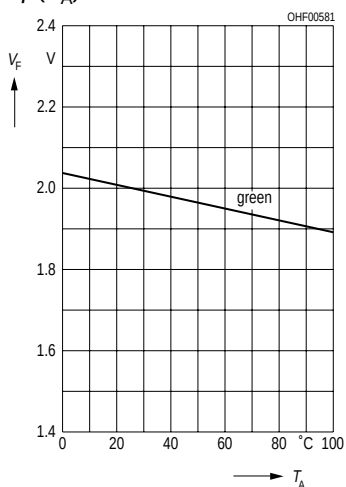
Wavelength at Peak Emission
 $\lambda_{\text{peak}} = f(T_A, I_F = 10\text{ mA})$



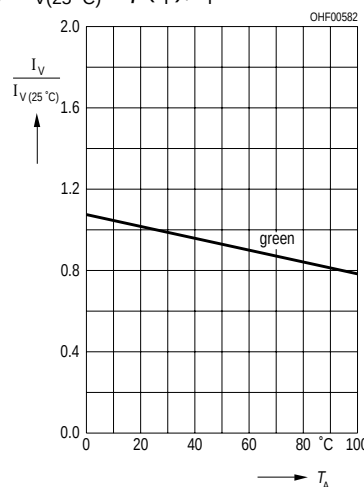
Dominant Wavelength
 $\lambda_{\text{dom}} = f(T_A, I_F = 10\text{ mA})$



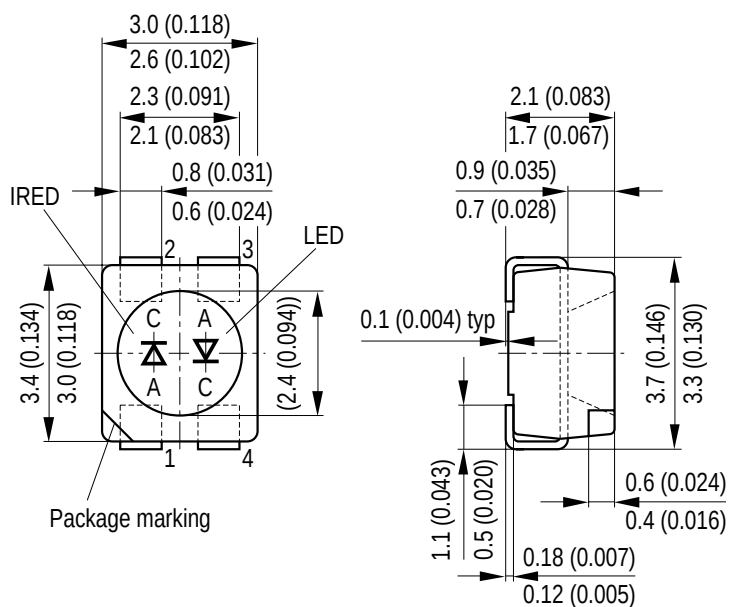
Forward Voltage $V_F = f(T_A)$
 $I_F = f(T_A)$



Relative Luminous Intensity
 $I_V / I_{V(25\text{ °C})} = f(I_F, T_A)$



Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).